

$$V_{CES} = 600V$$

$$I_C = 160A, T_C = 100^{\circ}C$$

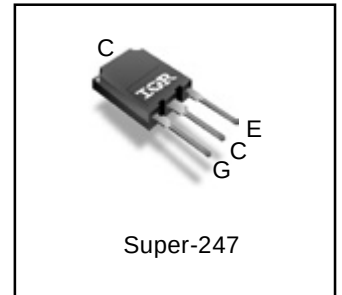
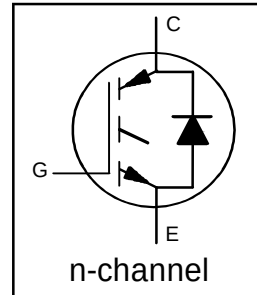
$$t_{SC} \geq 5\mu s, T_{J(max)} = 175^{\circ}C$$

$$V_{CE(on)} \text{ typ.} = 1.70V @ I_C = 120A$$

Applications

- Industrial Motor Drive
- Inverters
- UPS
- Welding

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE



G	C	E
Gate	Collector	Emitter

Features	Benefits
Low $V_{CE(ON)}$ and Switching Losses	High efficiency in a wide range of applications and switching frequencies
Square RBSOA and Maximum Junction Temperature $175^{\circ}C$	Improved reliability due to rugged hard switching performance and higher power capability
Positive $V_{CE(ON)}$ Temperature Coefficient	Excellent current sharing in parallel operation
$5\mu s$ short circuit SOA	Enables short circuit protection scheme
Lead-Free, RoHS compliant	Environmentally friendly

Base part number	Package Type	Standard Pack		Orderable part number
		Form	Quantity	
IRGPS46160DPbF	Super-247	Tube	25	IRGPS46160DPbF

Absolute Maximum Ratings

Parameter	Max.	Units
V_{CES}	600	V
$I_C @ T_C = 25^{\circ}C$	240⑥	A
$I_C @ T_C = 100^{\circ}C$	160	
I_{CM}	360	
I_{LM}	480	
$I_F @ T_C = 25^{\circ}C$	240⑥	
$I_F @ T_C = 100^{\circ}C$	160⑥	V
I_{FM}	480	
V_{GE}	± 20	W
	± 30	
$P_D @ T_C = 25^{\circ}C$	750	$^{\circ}C$
$P_D @ T_C = 100^{\circ}C$	375	
T_J	-55 to +175	
T_{STG}		
	300 (0.063 in. (1.6mm) from case)	
	10 lbf·in (1.1 N·m)	

Thermal Resistance

Parameter	Min.	Typ.	Max.	Units
R_{JC} (IGBT)	—	—	0.20	$^{\circ}C/W$
R_{JC} (Diode)	—	—	0.63	
R_{JCS}	—	0.24	—	
R_{JA}	—	—	40	

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 100\mu A$ ③
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.27	—	V/°C	$V_{GE} = 0V, I_C = 4.0mA$ (25°C-175°C)
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.70	2.05	V	$I_C = 120A, V_{GE} = 15V, T_J = 25^\circ\text{C}$
		—	2.15	—		$I_C = 120A, V_{GE} = 15V, T_J = 150^\circ\text{C}$
		—	2.20	—		$I_C = 120A, V_{GE} = 15V, T_J = 175^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	4.0	—	6.5	V	$V_{CE} = V_{GE}, I_C = 5.6mA$
$\Delta V_{GE(th)}/\Delta T_J$	Threshold Voltage temp. coefficient	—	-17	—	mV/°C	$V_{CE} = V_{GE}, I_C = 5.6mA$ (25°C - 175°C)
g_{fe}	Forward Transconductance	—	77	—	S	$V_{CE} = 50V, I_C = 120A$
I_{CES}	Collector-to-Emitter Leakage Current	—	1.0	150	μA	$V_{GE} = 0V, V_{CE} = 600V$
		—	2.3	—	mA	$V_{GE} = 0V, V_{CE} = 600V, T_J = 175^\circ\text{C}$
V_{FM}	Diode Forward Voltage Drop	—	2.4	3.0	V	$I_F = 120A$
		—	1.9	—		$I_F = 120A, T_J = 175^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±400	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge	—	240	—	nC	$I_C = 120A$ $V_{GE} = 15V$ $V_{CC} = 400V$
Q_{ge}	Gate-to-Emitter Charge	—	70	—		
Q_{gc}	Gate-to-Collector Charge	—	90	—		
E_{on}	Turn-On Switching Loss	—	5750	—	μJ	$I_C = 120A, V_{CC} = 400V, V_{GE} = 15V$ $R_G = 4.7\Omega, L = 66\mu H, T_J = 25^\circ C$
E_{off}	Turn-Off Switching Loss	—	3430	—		
E_{total}	Total Switching Loss	—	9180	—		
$t_{d(on)}$	Turn-On delay time	—	80	—	ns	Energy losses include tail & diode reverse recovery ⑤
t_r	Rise time	—	70	—		
$t_{d(off)}$	Turn-Off delay time	—	190	—		
t_f	Fall time	—	40	—		
E_{on}	Turn-On Switching Loss	—	7740	—	μJ	$I_C = 120A, V_{CC} = 400V, V_{GE}=15V$ $R_G = 4.7\Omega, L = 66\mu H, T_J = 175^\circ C$ Energy losses include tail & diode reverse recovery ⑤
E_{off}	Turn-Off Switching Loss	—	4390	—		
E_{total}	Total Switching Loss	—	12130	—		
$t_{d(on)}$	Turn-On delay time	—	80	—	ns	
t_r	Rise time	—	75	—		
$t_{d(off)}$	Turn-Off delay time	—	230	—		
t_f	Fall time	—	55	—		
C_{ies}	Input Capacitance	—	7750	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0Mhz$
C_{oes}	Output Capacitance	—	550	—		
C_{res}	Reverse Transfer Capacitance	—	225	—		
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				$T_J = 175^\circ C, I_C = 480A$ $V_{CC} = 480V, V_p \leq 600V$ $R_g = 4.7\Omega, V_{GE} = +20V$ to 0V
SCSOA	Short Circuit Safe Operating Area	5	—	—	μs	$V_{CC} = 400V, V_p \leq 600V$ $R_g = 4.7\Omega, V_{GE} = +15V$ to 0V
E_{rec}	Reverse Recovery Energy of the Diode	—	500	—	μJ	$T_J = 175^\circ C$
t_{rr}	Diode Reverse Recovery Time	—	130	—	ns	$V_{CC} = 400V, I_F = 120A$
I_{rr}	Peak Reverse Recovery Current	—	36	—	A	$V_{GE} = 15V, R_g = 4.7\Omega, L = 100\mu H$

Notes:

- $V_{CC} = 80\% (V_{CES}), V_{GE} = 20V, L = 66\mu H, R_G = 4.7\Omega$, tested in production $I_{LM} \leq 400A$.
- Pulse width limited by max. junction temperature.
- Refer to AN-1086 for guidelines for measuring $V_{(BR)CES}$ safely.
- R_θ is measured at T_J of approximately 90°C .
- Values influenced by parasitic L and C in measurement.
- Calculated continuous current based on maximum allowable junction temperature. Package IGBT current limit is 195A. Package diode current limit is 120A. Note that current limitations arising from heating of the device leads may occur.

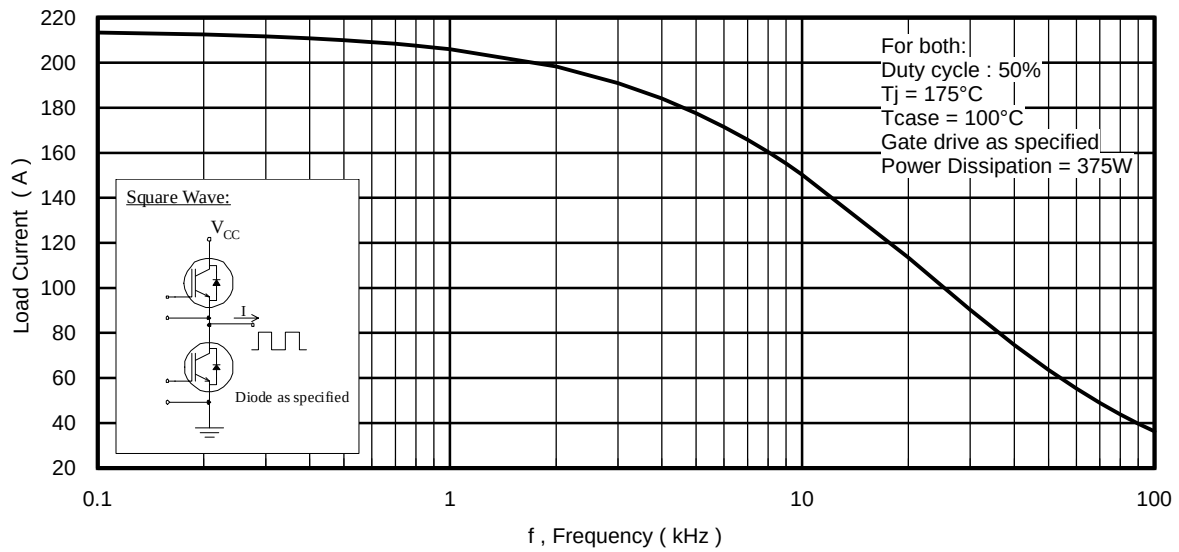


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

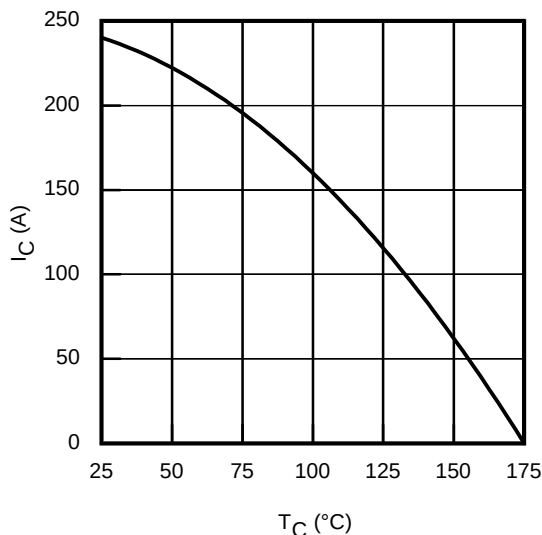


Fig. 2 - Maximum DC Collector Current vs. Case Temperature

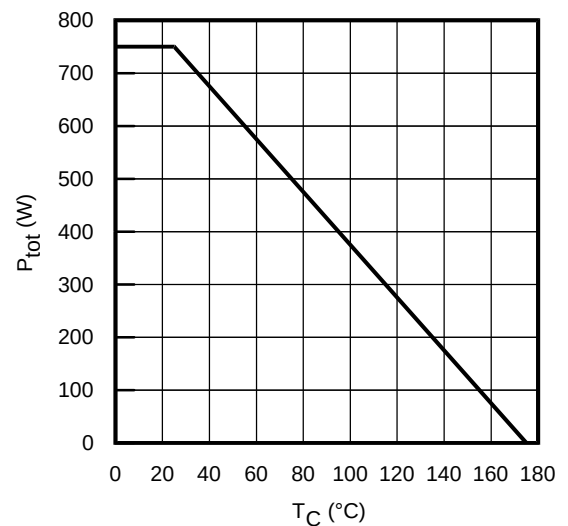


Fig. 3 - Power Dissipation vs. Case Temperature

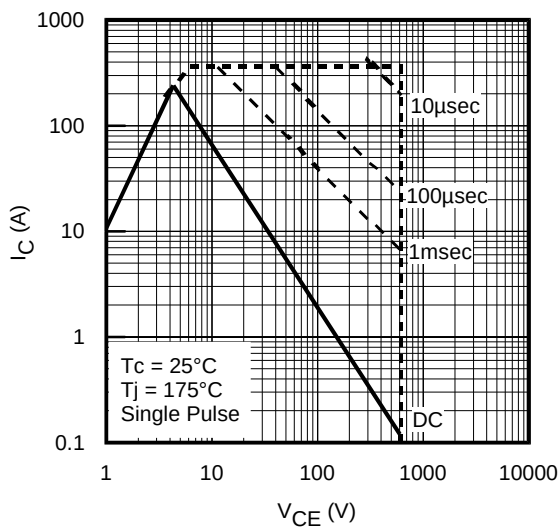


Fig. 4 - Forward SOA
 $T_C = 25^{\circ}\text{C}$, $T_J \leq 175^{\circ}\text{C}$; $V_{\text{GE}} = 15\text{V}$

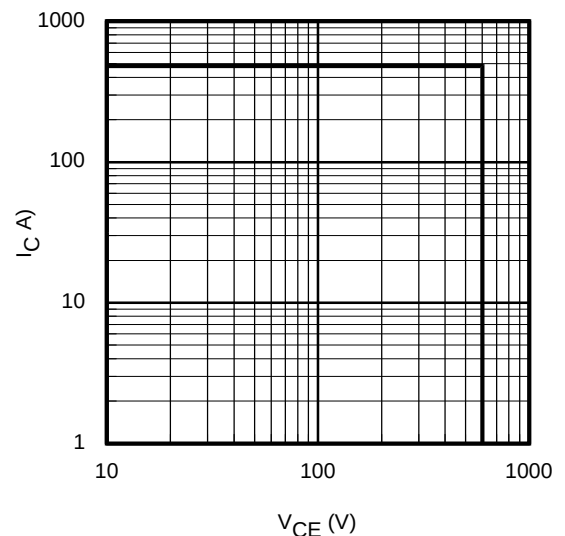


Fig. 5 - Reverse Bias SOA
 $T_J = 175^{\circ}\text{C}$; $V_{\text{GE}} = 20\text{V}$

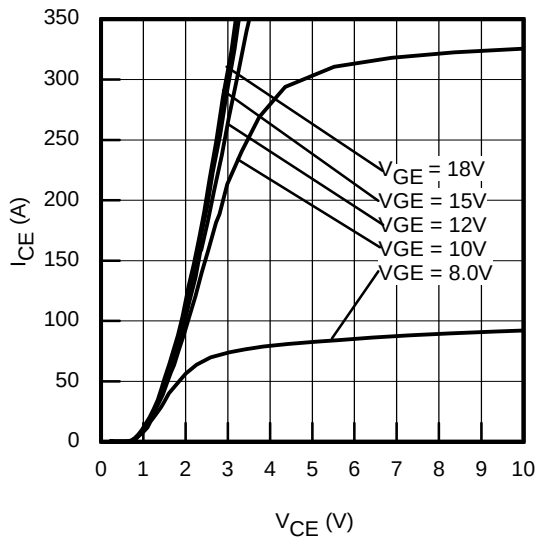


Fig. 6 - Typ. IGBT Output Characteristics
 $T_J = -40^{\circ}\text{C}$; $t_p = 80\mu\text{s}$

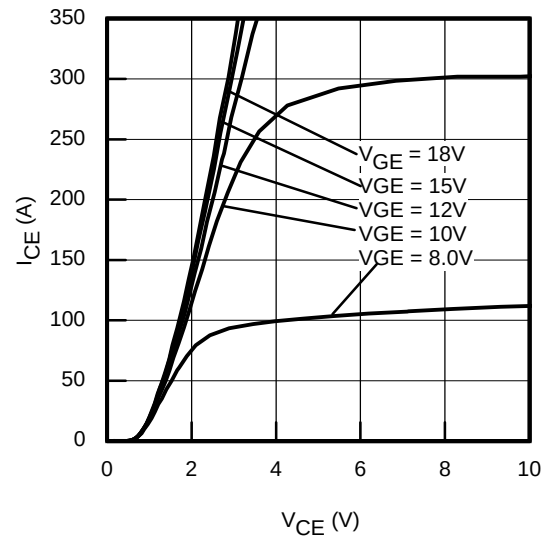


Fig. 7 - Typ. IGBT Output Characteristics
 $T_J = 25^{\circ}\text{C}$; $t_p = 80\mu\text{s}$

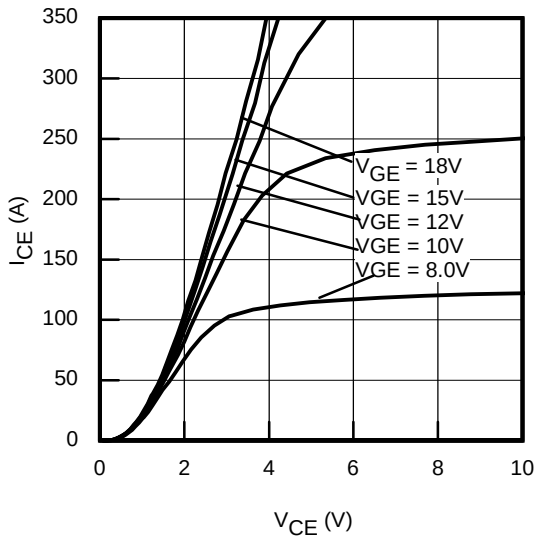


Fig. 8 - Typ. IGBT Output Characteristics
 $T_J = 175^{\circ}\text{C}$; $t_p = 80\mu\text{s}$

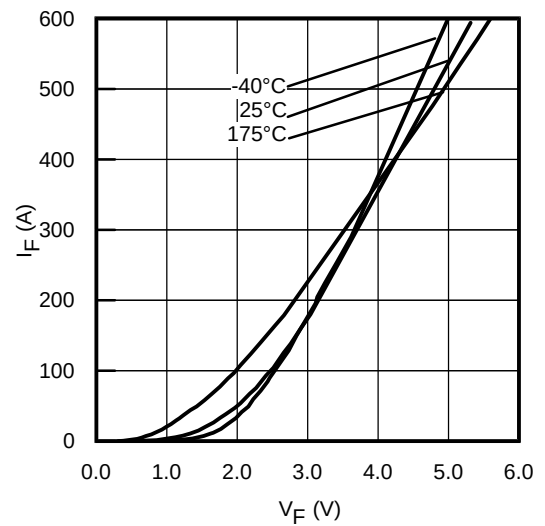


Fig. 9 - Typ. Diode Forward Characteristics
 $t_p = 80\mu\text{s}$

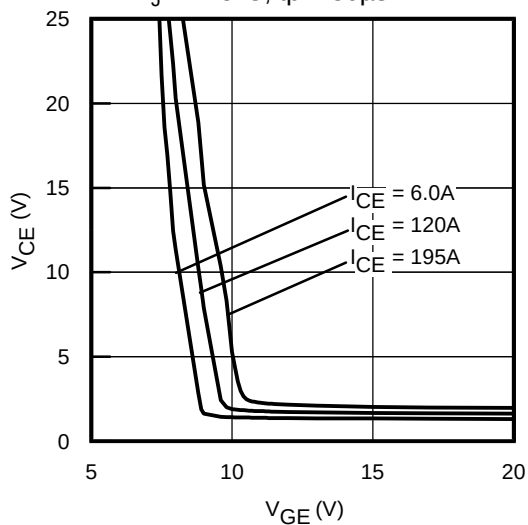


Fig. 10 - Typical V_{CE} vs. V_{GE}
 $T_J = -40^{\circ}\text{C}$

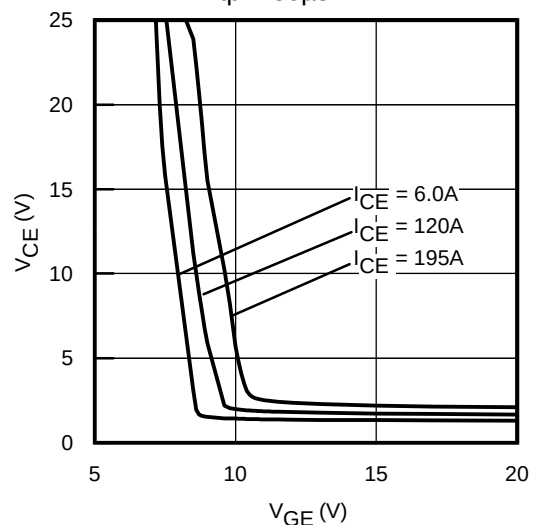


Fig. 11 - Typical V_{CE} vs. V_{GE}
 $T_J = 25^{\circ}\text{C}$

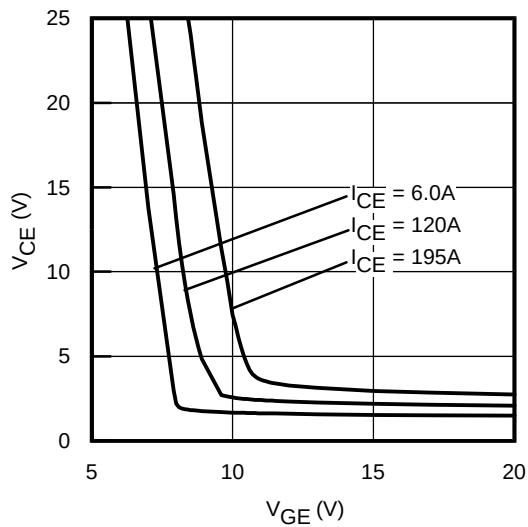


Fig. 12 - Typical V_{CE} vs. V_{GE}
 $T_J = 175^\circ\text{C}$

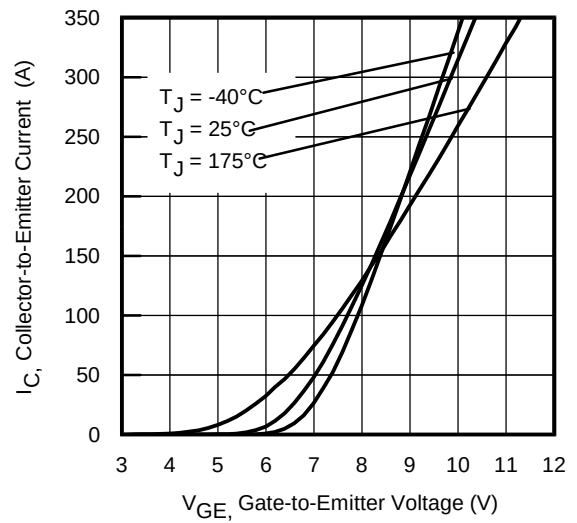


Fig. 13 - Typ. Transfer Characteristics
 $V_{CE} = 50\text{V}$; $t_p = 10\mu\text{s}$

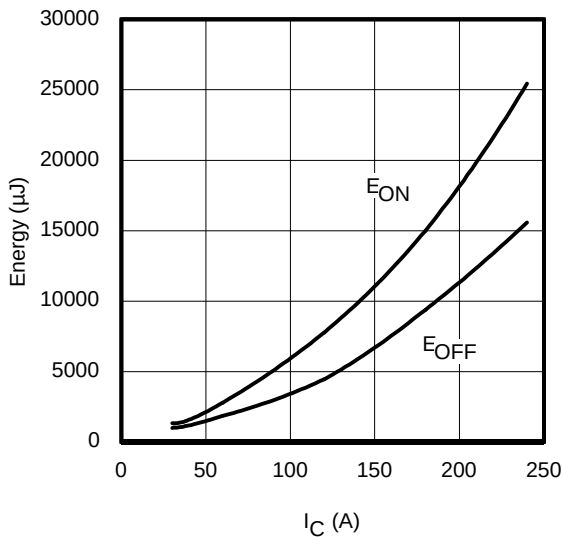


Fig. 14 - Typ. Energy Loss vs. I_C
 $T_J = 175^\circ\text{C}$; $L = 66\mu\text{H}$; $V_{CE} = 400\text{V}$; $R_G = 4.7\Omega$; $V_{GE} = 15\text{V}$

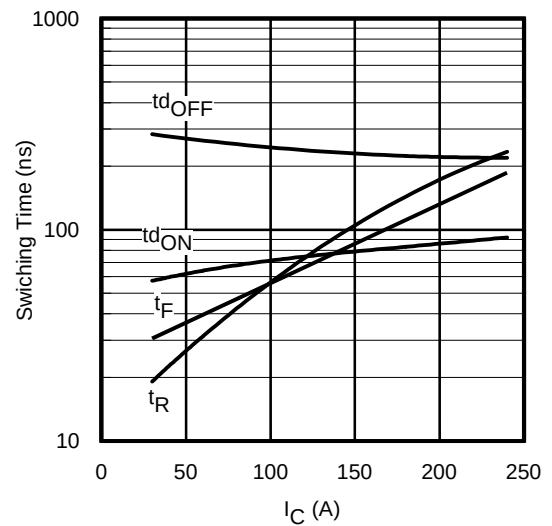


Fig. 15 - Typ. Switching Time vs. I_C
 $T_J = 175^\circ\text{C}$; $L = 66\mu\text{H}$; $V_{CE} = 400\text{V}$; $R_G = 4.7\Omega$; $V_{GE} = 15\text{V}$

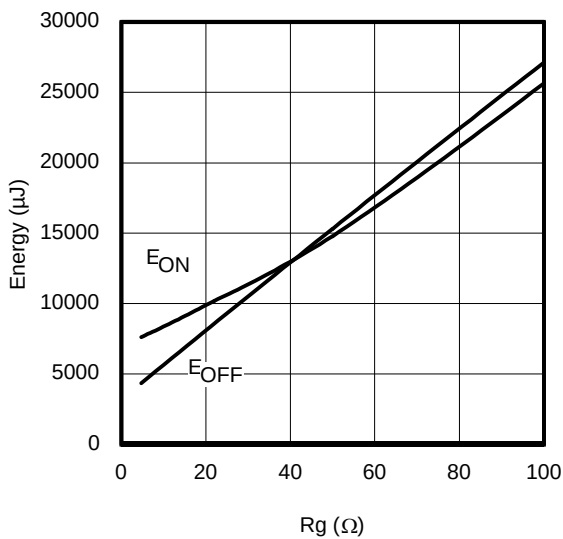


Fig. 16 - Typ. Energy Loss vs. R_G
 $T_J = 175^\circ\text{C}$; $L = 66\mu\text{H}$; $V_{CE} = 400\text{V}$; $I_{CE} = 120\text{A}$; $V_{GE} = 15\text{V}$

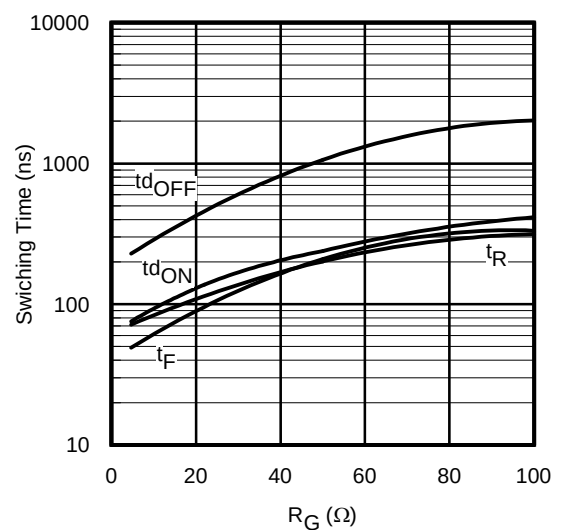


Fig. 17 - Typ. Switching Time vs. R_G
 $T_J = 175^\circ\text{C}$; $L = 66\mu\text{H}$; $V_{CE} = 400\text{V}$; $I_{CE} = 120\text{A}$; $V_{GE} = 15\text{V}$

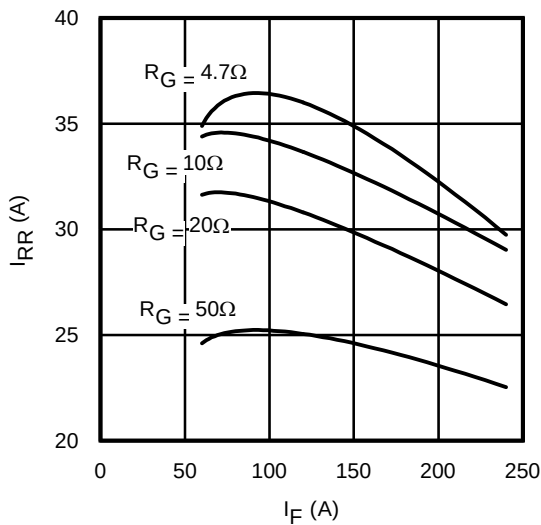


Fig. 18 - Typ. Diode I_{RR} vs. I_F
 $T_J = 175^\circ\text{C}$

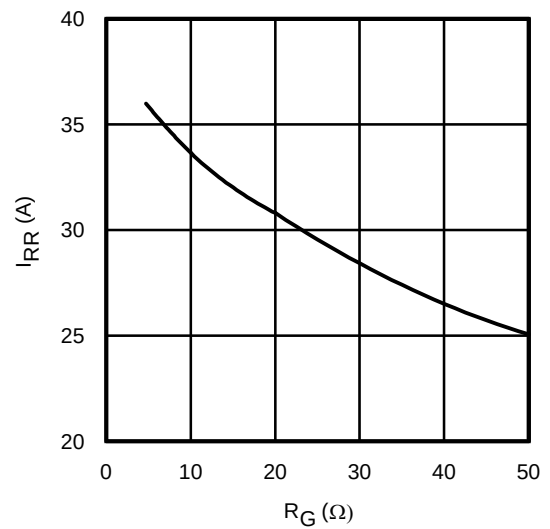


Fig. 19 - Typ. Diode I_{RR} vs. R_G
 $T_J = 175^\circ\text{C}$

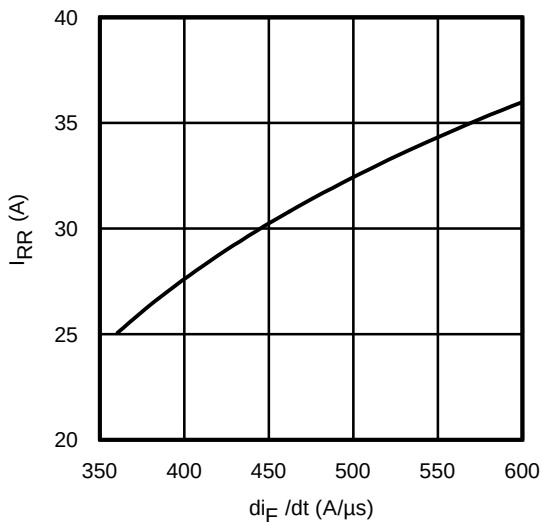


Fig. 20 - Typ. Diode I_{RR} vs. di_F/dt
 $V_{CC} = 400\text{V}$; $V_{GE} = 15\text{V}$; $I_F = 120\text{A}$; $T_J = 175^\circ\text{C}$

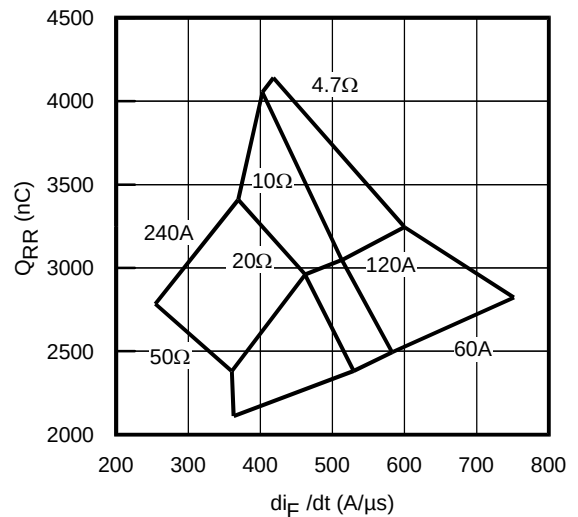


Fig. 21 - Typ. Diode Q_{RR} vs. di_F/dt
 $V_{CC} = 400\text{V}$; $V_{GE} = 15\text{V}$; $T_J = 175^\circ\text{C}$

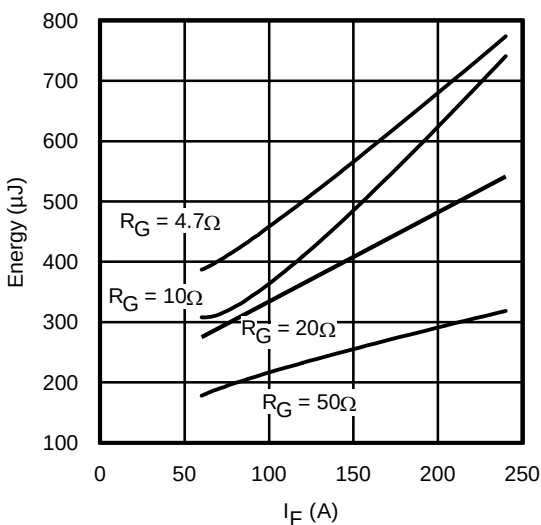


Fig. 22 - Typ. Diode E_{RR} vs. I_F
 $T_J = 175^\circ\text{C}$

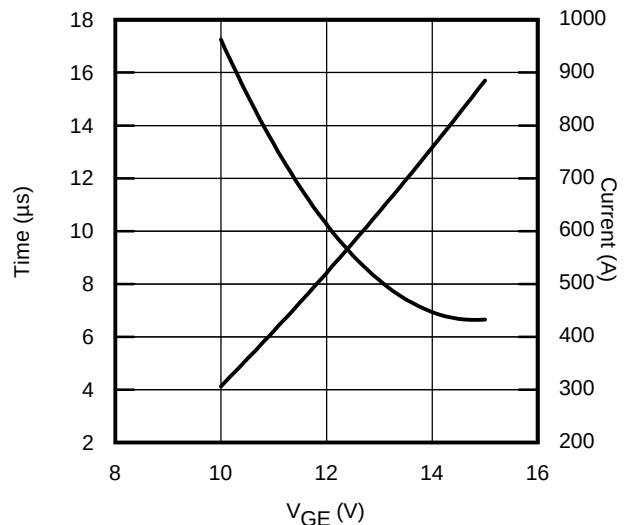


Fig. 23 - V_{GE} vs. Short Circuit Time
 $V_{CC} = 400\text{V}$; $T_C = 25^\circ\text{C}$

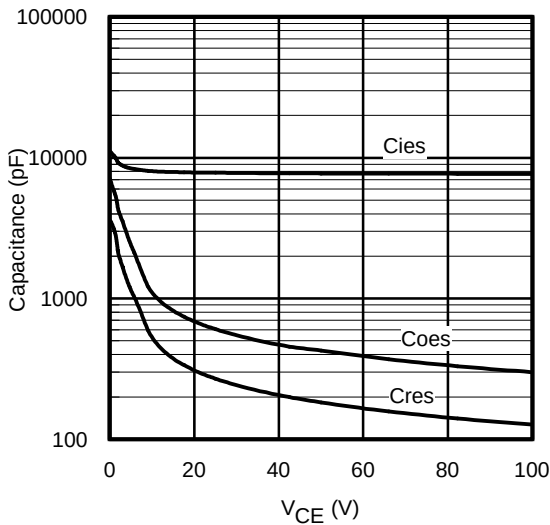


Fig. 24 - Typ. Capacitance vs. V_{CE}
 $V_{GE} = 0V$; $f = 1MHz$

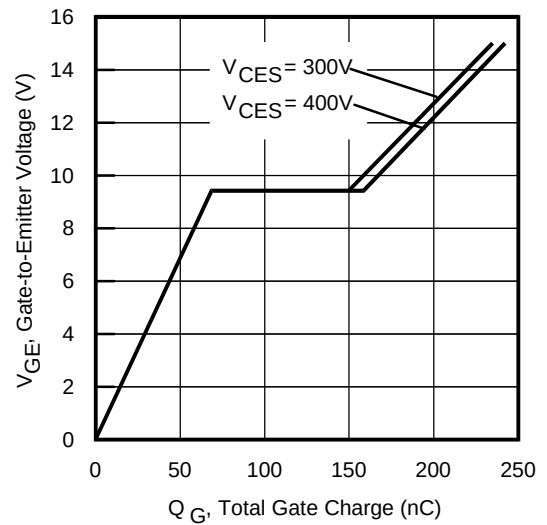


Fig. 25 - Typical Gate Charge vs. V_{GE}
 $I_{CE} = 120A$; $L = 100\mu H$

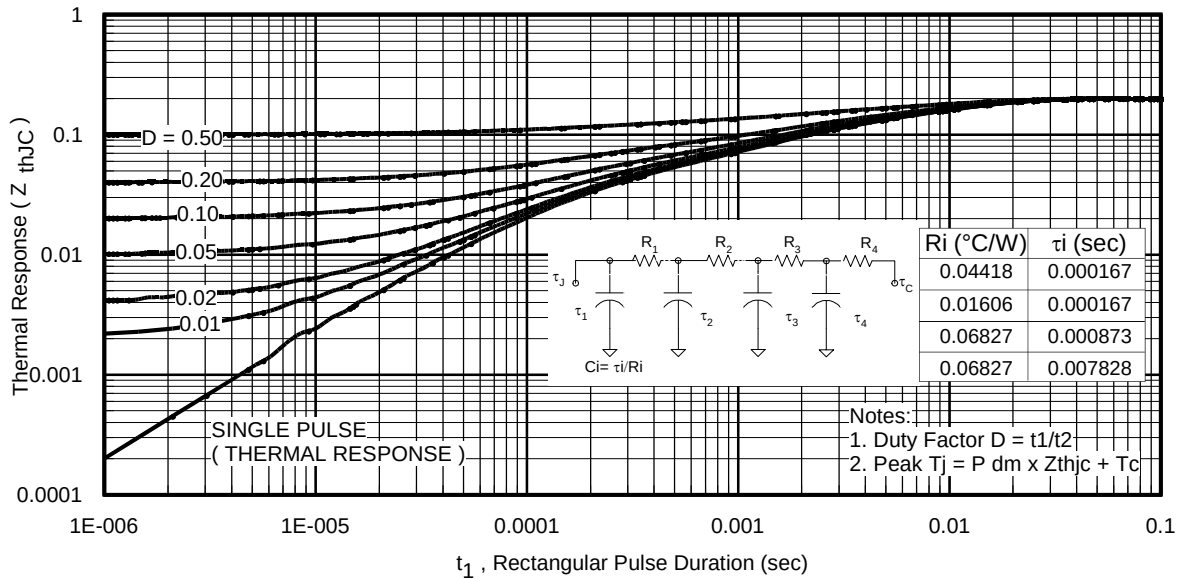


Fig. 26. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

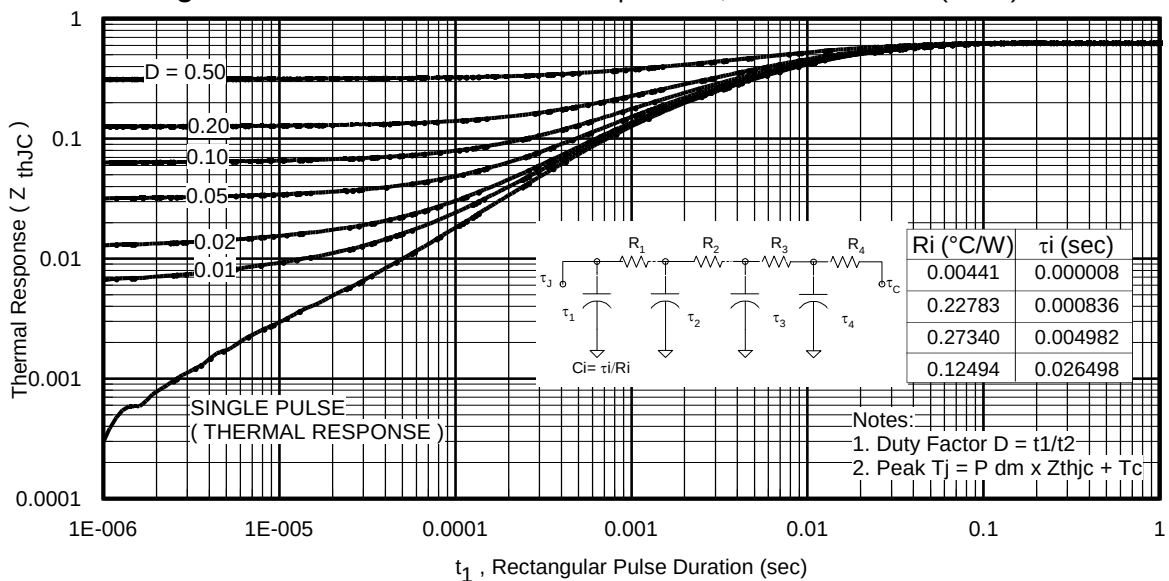


Fig. 27. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)

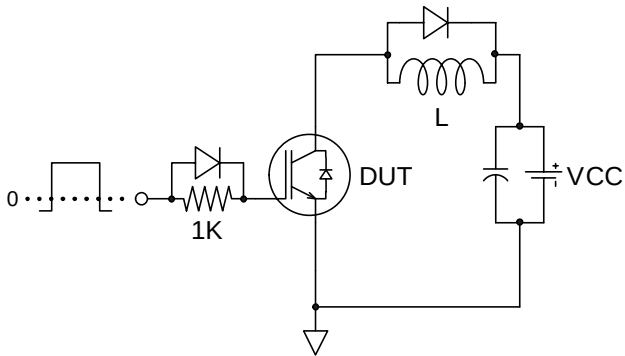


Fig.C.T.1 - Gate Charge Circuit (turn-off)

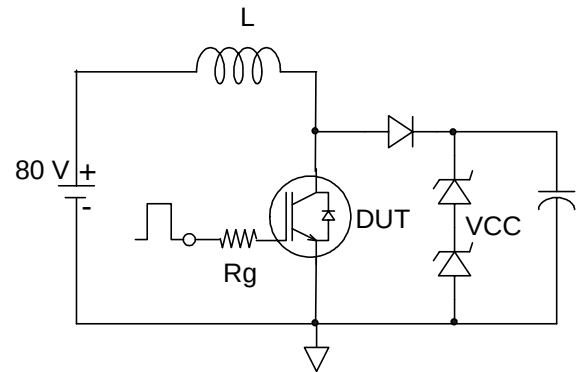


Fig.C.T.2 - RBSOA Circuit

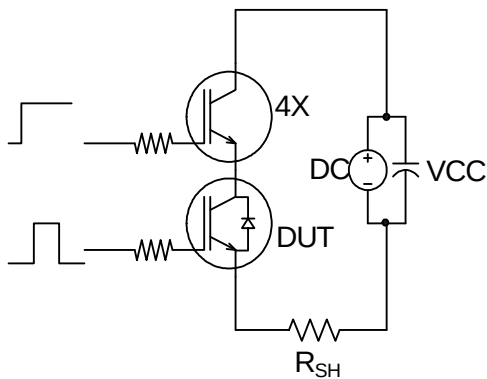


Fig.C.T.3 - S.C. SOA Circuit

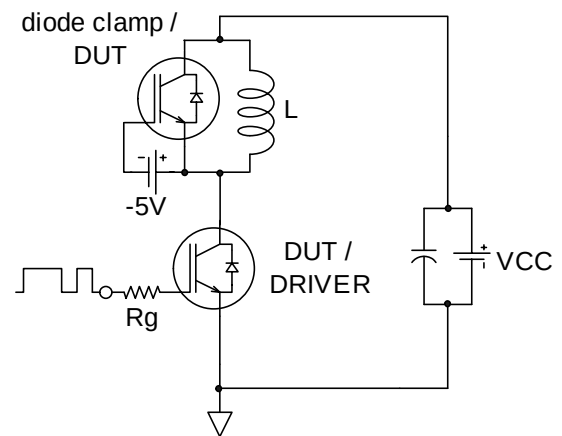


Fig.C.T.4 - Switching Loss Circuit

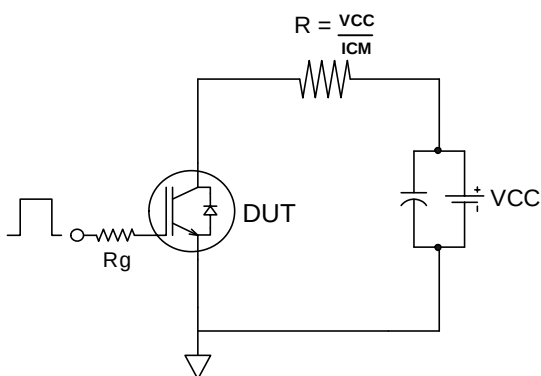


Fig.C.T.5 - Resistive Load Circuit

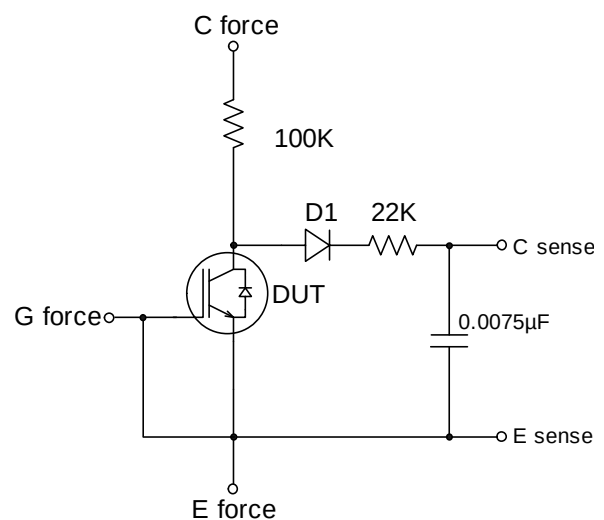


Fig.C.T.6 - BVCES Filter Circuit

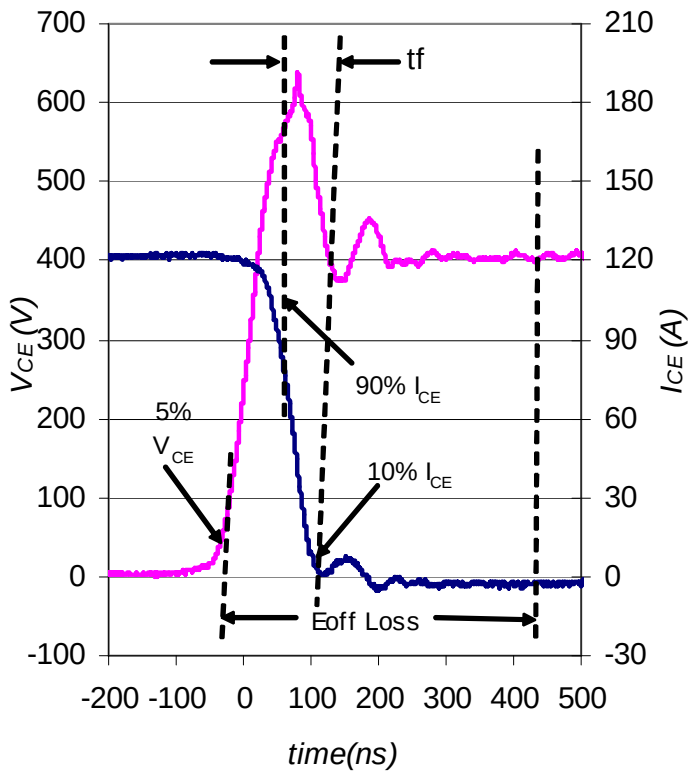


Fig. WF1 - Typ. Turn-off Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

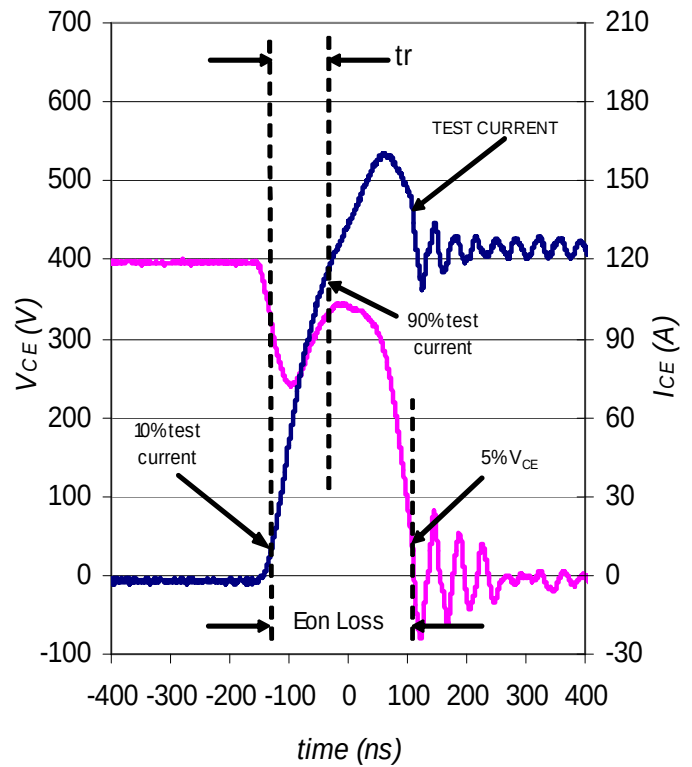


Fig. WF2 - Typ. Turn-on Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

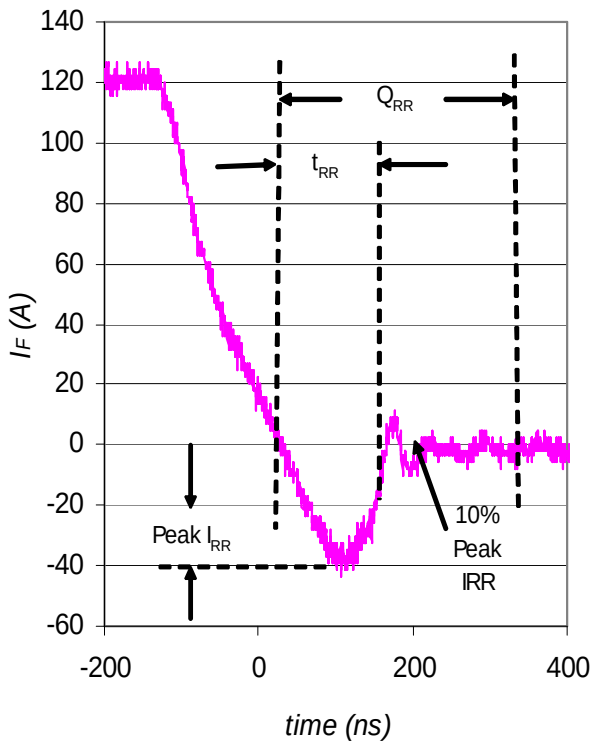


Fig. WF3 - Typ. Diode Recovery Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

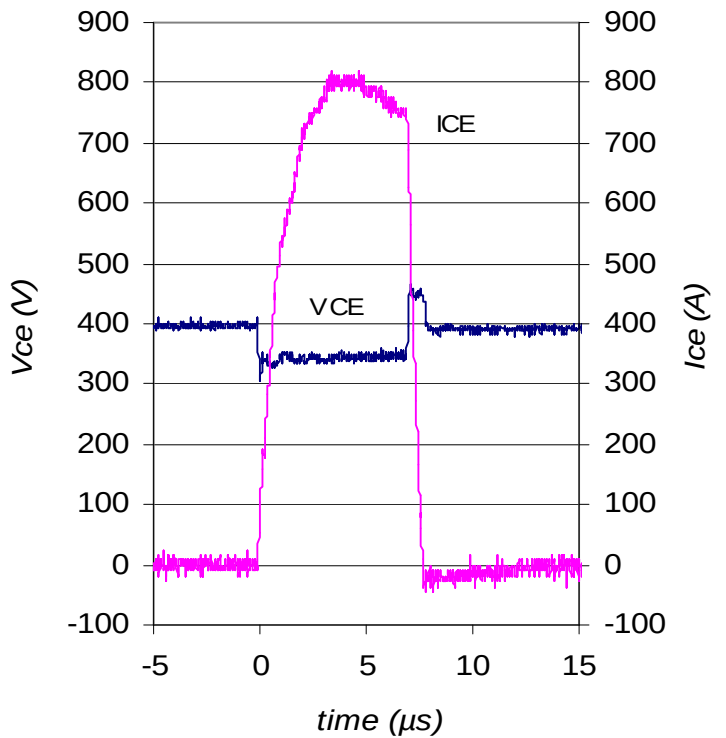
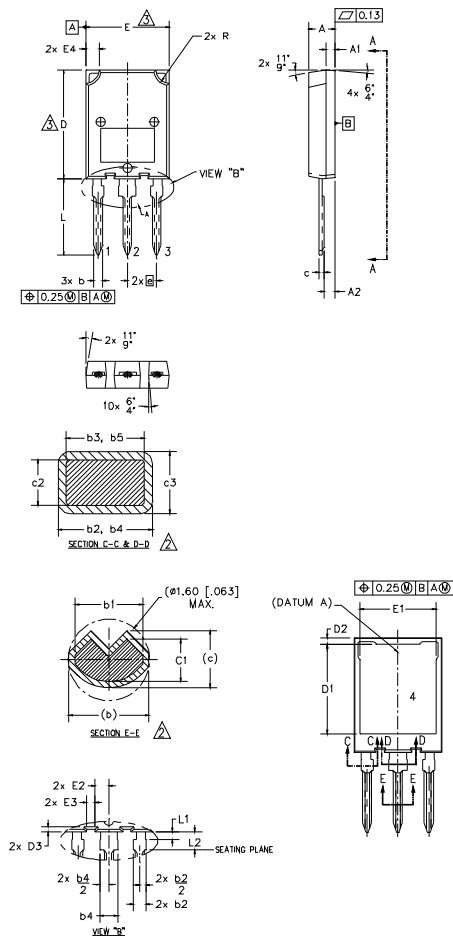


Fig. WF4 - Typ. S.C. Waveform
@ $T_J = 25^\circ\text{C}$ using Fig. CT.3

Case Outline and Dimensions — Super-247



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M-1994
2. DIMENSIONS b1, b3, b5, c1 & c3 APPLY TO BASE METAL ONLY.
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTER EXTREMES OF THE PLASTIC BODY.
4. ALL DIMENSIONS SHOWN IN MILLIMETERS.
5. CONTROLLING DIMENSION: MILLIMETER.
6. OUTLINE CONFORMS TO JEDEC OUTLINE TO-274AA

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.90	5.10	.193	.201	
A1	1.70	2.10	.067	.083	
A2	2.19	2.39	.086	.094	
b	1.25	1.55	.049	.061	
b1	1.20	1.50	.047	.059	2
b2	2.00	2.30	.079	.091	
b3	1.92	2.22	.076	.087	2
b4	2.96	3.52	.116	.139	
b5	2.90	3.46	.114	.136	2
c	0.86	1.16	.034	.046	
c1	0.80	1.10	.031	.043	2
c2	0.65	0.85	.026	.033	
c3	0.50	0.70	.020	.028	2
D	20.16	20.44	.794	.805	3
D1	15.50	15.80	.610	.622	
D2	0.87	1.17	.034	.046	
D3	0.80	1.26	.031	.050	
E	15.20	15.80	.598	.622	3
E1	13.40	13.80	.528	.543	
E2	1.42	3.23	.056	.127	
E3	1.20	1.60	.047	.063	
E4	2.00	3.00	.079	.118	
e	5.45 BSC		.215 BSC		
L	13.82	14.58	.544	.574	
L1	1.10	1.50	.043	.059	
L2	2.85	3.61	.112	.142	
R	2.00	3.00	.079	.118	

LEAD ASSIGNMENTS

MOSFET

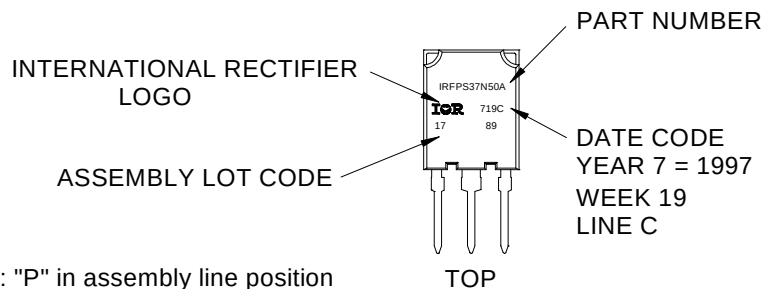
- 1.— GATE
- 2.— DRAIN
- 3.— SOURCE
- 4.— DRAIN

IGBT

- 1.— GATE
- 2.— COLLECTOR
- 3.— EMITTER
- 4.— COLLECTOR

Super-247 (TO-274AA) Part Marking Information

EXAMPLE: THIS IS AN IRFPS37N50A WITH
ASSEMBLY LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"



Note: "P" in assembly line position
indicates "Lead-Free"

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Qualification Information[†]

Qualification Level		Industrial (per International Rectifier's internal guidelines)	
Moisture Sensitivity Level		Super-247	N/A
ESD	Human Body Model	Class H3B (8000V) ^{††} AEC-Q101-001	
	Charged Device Model	Class C5 (1125V) ^{††} AEC-Q101-005	
RoHS Compliant		Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>

†† Highest passing voltage.

Revision History

Date	Comments
11/14/2014	- Added note ④ to I_{FM} Diode Maximum Forward Current on page 1. - Added note ⑤ to switching losses test condition on page 2.
09/20/2019	Change of package dimensions